



Features:

- Glass passivated chip junction
- High efficiency, low V_F
- High current capability
- High reliability
- High surge current capability
- Low power loss

Specifications:

Mechanical Data:

Cases	: Moulded plastic
Lead	: Pure tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
Polarity	: Colour band denotes cathode end
High temperature soldering guaranteed	: 260°C/10 seconds/0.375", (9.5mm) lead lengths at 5lbs., (2.3kg) tension
Weight	: 0.34g

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

Type Number	Symbol	FR103G	FR105G	FR107G	Units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	200	600	1,000	V
Maximum RMS Voltage	V _{RMS}	140	420	700	
Maximum DC Blocking Voltage	V _{DC}	200	600	1,000	
Maximum Average Forward Rectified Current 0.375" (9.5mm) Lead Length at T _A = 55°C	I _(AV)	1			A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	30			
Maximum Instantaneous Forward Voltage at 1A	V _F	1.3			V

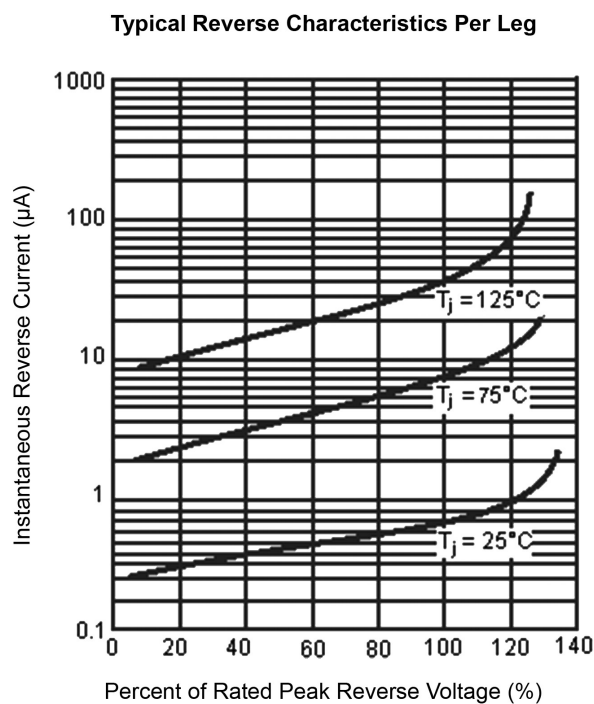
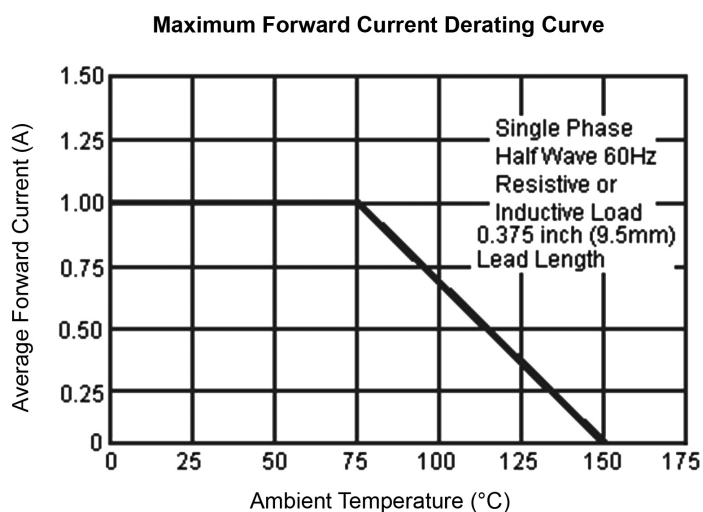
Type Number	Symbol	FR103G	FR105G	FR107G	Units
Maximum DC Reverse Current at $T_A = 25^\circ\text{C}$ at Rated DC Blocking Voltage at $T_A = 125^\circ\text{C}$	I_R	5 150			μA μA
Maximum Reverse Recovery Time (Note 1)	T_{rr}	150	250	500	nS
Typical Junction Capacitance (Note 2)	C_j	10			pF
Typical Thermal Resistance	$R_{\theta JA}$	70			$^\circ\text{C/W}$
Operating Temperature Range	T_J	-65 to +150			$^\circ\text{C}$
Storage Temperature Range	T_{STG}				

Note: 1. Reverse Recovery Test Conditions: $I_F = 0.5\text{A}$, $I_R = 1\text{A}$, $I_{RR} = 0.25\text{A}$.

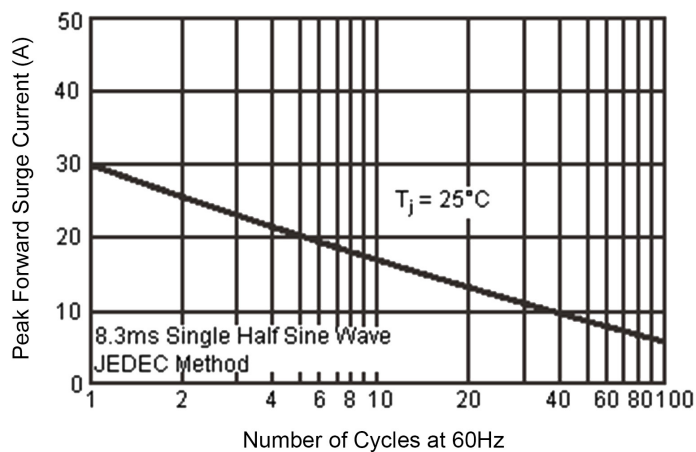
Note: 2. Measured at 1MHz and Applied Reverse Voltage of 4V DC.

Note: 3. Mount on Cu-Pad Size 5mm $\times$ 5mm on PCB.

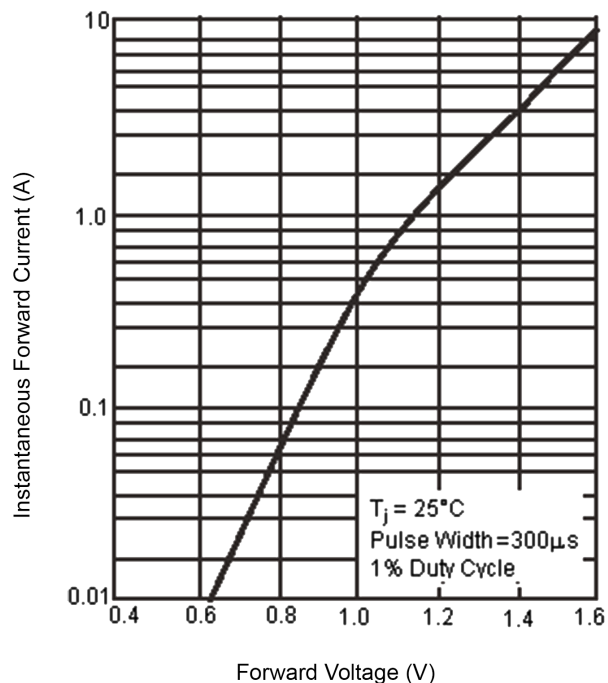
Ratings and Characteristic Curves (FR103G, FR105G, FR107G)



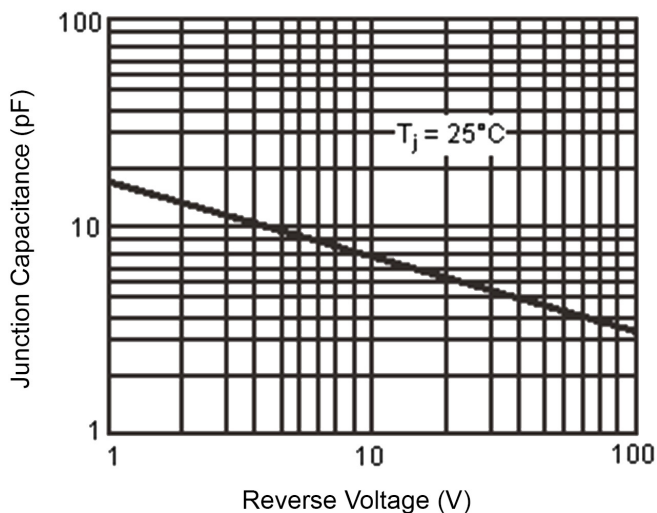
Maximum Non-Repetitive Forward
Surge Current



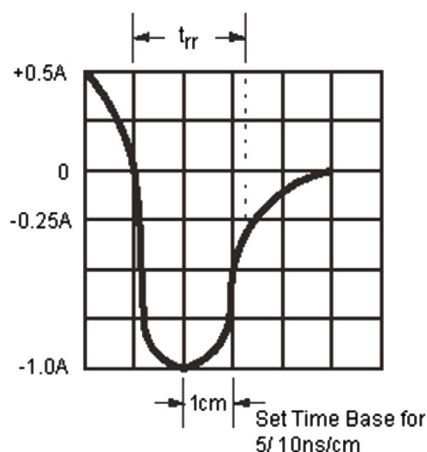
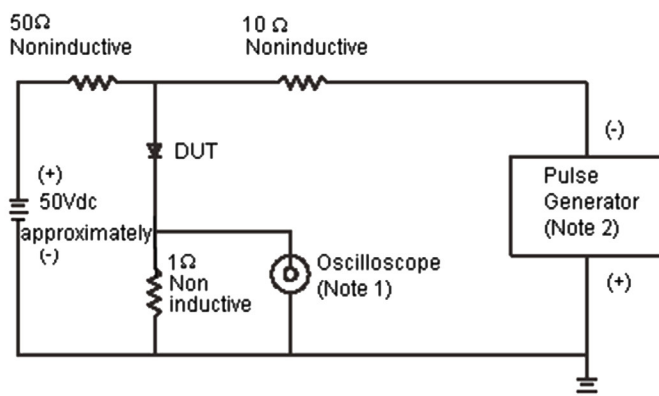
Typical Forward Characteristics



Typical Junction Capacitance



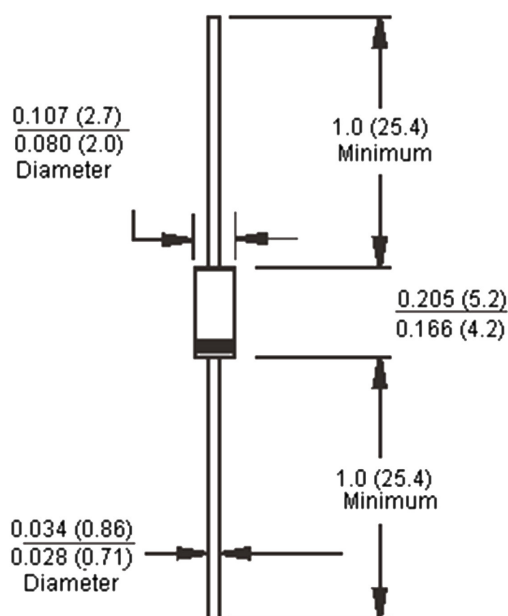
Reverse Recovery Time Characteristic and Test Circuit Diagram



Note: 1. Rise Time = 7ns Maximum. Input Impedance = 1MΩ 22pf

Note: 2. Rise Time = 10ns Maximum Source Impedance = 50Ω

DO-41



Dimensions : Inches (Millimetres)

Part Number Table

Description	Part Number
Diode, Fast, 1A, 200V	FR103G
Diode, Fast, 1A, 600V	FR105G
Diode, Fast, 1A, 1,000V	FR107G

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